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	Nota di contenuto	Preface; Acknowledgements; Contents; Abbreviations; Symbols with Units; About the Authors; Part I Review of Fundamentalsof Semiconductors; 1 Semiconductor Materials: Their Properties, Applications, and Recent Advances; Abstract; 1.1 Importance of Electronic and Semiconducting Materials; 1.2 Classification of Electrical and Electronic Materials, and Status of Semiconducting Materials; 1.2.1 Conductors; 1.2.2 Semiconductors; 1.2.3 Dielectrics; 1.2.4 Superconductors; 1.3 Scope of Application of Semiconducting Materials; 1.4 Electrons and Their Role in Semiconductivity; 1.4.1 Valence Electrons 1.5 Classification of Materials on the Basis of Energy Gap (or Band)1.5.1 Valence and Conduction Band, and Energy Gap; 1.5.2 Comparison among Conductors, Semiconductors and Insulators; 1.6 Introduction to Semiconducting Materials [1]; 1.6.1 Different Types of Semiconducting Materials; 1.6.2 Merits of Semiconducting Materials; 1.6.3 Characteristics of Semiconducting Materials; 1.6.4 Semiconducting Devices and Their Working Principles; 1.7 Element Form

	Semiconducting Materials; 1.7.1 Silicon (Si); 1.7.2 Germanium (Ge); 1.7.3 Selenium (Se); 1.7.4 Antimony (Sb); 1.7.5 Other Elements 1.7.6 Comparison Between Silicon and Germanium1.8 Formulated (Compound and Alloyed) Semiconductor Materials; 1.8.1 Gallium Arsenide (GaAs); 1.8.2 Indium Antimonite (InSb); 1.8.3 Oxides, Sulphides, Hallides, Tellurides and Sellurides; 1.8.4 Cadmium Sulphide (CdS); 1.8.5 Silicon Carbide (SiC); 1.8.6 Lead Sulphide (PbS); 1.8.7 Indium Arsenide (InAs); 1.9 Choicest Materials for Different Semiconductor Devices; 1.10 Spintronics and Spintronic Materials [1]; 1.10.1 Major Fields of Spintronic Research; 1.10.2 Operational Mechanisms of Spintronic Devices 1.10.3 Working Principle of Spintronic Devices1.10.4 Emerging and Futuristic Spintronic Materials; 1.11 Ferromagnetic Semiconductor; 1.12 Emerging Wide Bandgap Semiconductors; 1.13 Left Handed (LH) Materials [1]; 1.13.1 Single Negative Left-Handed Materials; 1.13.2 Double Negative Left-Handed Materials; 1.13.3 Negative Index Metamaterials; 1.13.4 Double Positive Medium; 1.14 Manganese Semiconductor; 1.15 Diluted Magnetic Semiconductor; 1.16 Silicon: The Semiconductor Used as Raw Material in Making ICs; 1.16.1 Gallium Arsenide (GaAs) for Making Integrated Circuit 1.17 Semiconductors in Cricket; 1.19 Glimpse of Some Salient Semiconductors in Cricket; 1.19 Glimpse of Some Salient Semiconductors in Cricket; 1.19 Glimpse of Some Salient Semiconductors and, Semiconductor Devices; Abstract; 2.1 Crystal Structure; 2.2 Bravais Crystal System; 2.3 Miller Indices: The Crystallographic Notation of Atomic Planes; 2.3.1 Determining the Miller Indices of a Given Plane [1] 2.3.2 Family of Planes
Sommario/riassunto	This book presents the latest developments in semiconducting materials and devices, providing up-to-date information on the science, processes, and applications in the field. A wide range of topics are covered, including optoelectronic devices, metal–semiconductor junctions, heterojunctions, MISFETs, LEDs, semiconductor lasers, photodiodes, switching diodes, tunnel diodes, Gunn diodes, solar cells, varactor diodes, IMPATT diodes, and advanced semiconductors. Detailed attention is paid to advanced and futuristic materials. In addition, clear explanations are provided of, for example, electron theories, high-field effects, the Hall effect, transit-time effects, drift and diffusion, breakdown mechanisms, equilibrium and transient conditions, switching, and biasing. The book is designed to meet the needs of undergraduate engineering students and will also be very useful for postgraduate students; it will assist in preparation for examinations at colleges and universities and for other examinations in engineering. Practice questions are therefore presented in both essay and multiple choice format, and many solved examples and unsolved problems are included.